

2SD875

Silicon NPN epitaxial planer type

For low-frequency power amplification

Complementary to 2SB767

■ Features

- Large collector power dissipation P_C .
- High collector to emitter voltage V_{CEO} .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	80	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	1	A
Collector current	I_C	0.5	A
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

* Printed circuit board: Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion

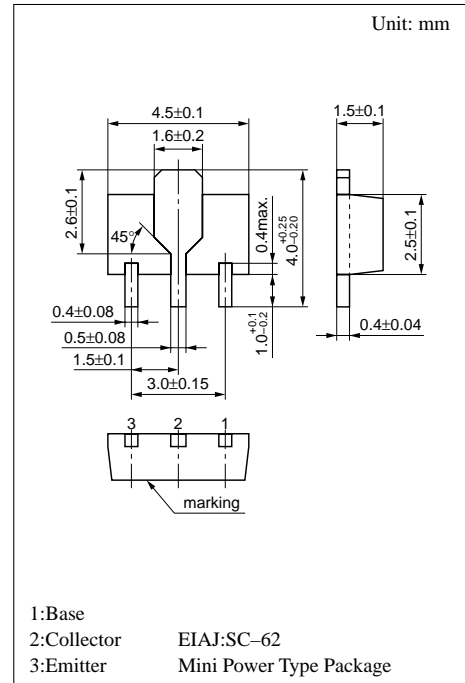
■ Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			0.1	μA
Collector to base voltage	V_{CBO}	$I_C = 10\mu\text{A}, I_E = 0$	80			V
Collector to emitter voltage	V_{CEO}	$I_C = 100\mu\text{A}, I_B = 0$	80			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu\text{A}, I_C = 0$	5			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = 10\text{V}, I_C = 150\text{mA}^{*2}$	130		330	
	h_{FE2}	$V_{CE} = 5\text{V}, I_C = 500\text{mA}^{*2}$	50	100		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300\text{mA}, I_B = 30\text{mA}^{*2}$		0.2	0.4	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 300\text{mA}, I_B = 30\text{mA}^{*2}$		0.85	1.2	V
Transition frequency	f_T	$V_{CB} = 10\text{V}, I_E = -50\text{mA}^{*2}, f = 200\text{MHz}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		11		pF

^{*2} Pulse measurement

^{*1} h_{FE1} Rank classification

Rank	R	S
h_{FE1}	130 ~ 220	185 ~ 330
Marking Symbol	XR	XS



Marking symbol : X

